



# TEA2093TS

GreenChip synchronous rectifier controller

Rev. 1 — 7 June 2022

Product data sheet

## 1 General description

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The TEA2093TS is a member of a new generation of synchronous rectifier (SR) controller ICs for switched mode power supplies. It includes an adaptive gate drive for maximum efficiency at any load.

The TEA2093TS is a dedicated controller IC for synchronous rectification on the secondary side of asymmetrical half-bridge flyback and standard flyback converters. It incorporates the sensing stage and driver stage for driving the SR MOSFET, which is rectifying the output of the secondary transformer winding.

The TEA2093TS can generate its own supply voltage for battery-charging applications with low output voltage or for applications with high-side rectification.

The TEA2093TS is fabricated in a silicon-on-insulator (SOI) process.

## 2 Features and benefits

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### 2.1 Efficiency features

- Adaptive gate drive for maximum efficiency at any load
- Typical supply current in no-load operation below 200  $\mu$ A

### 2.2 Application features

- Operates in a wide output voltage range down to 0 V
- Drain sense pin capable of handling input voltages up to 120 V
- Self-supplying for operation with low output voltage
- Self-supplying for high-side rectification without the use of an auxiliary winding
- Operates with standard and logic level SR MOSFETs
- Supports USB BC, USB PD, and quick charge applications
- TSOP6 package

### 2.3 Control features

- Adaptive gate drive for fast turn-off at the end of conduction
- Undervoltage lockout (UVLO) with active gate pull-down



### 3 Applications

The TEA2093TS is intended for flyback power supplies. In such applications, it can drive the external synchronous rectifier MOSFET, which replaces the diode for the rectification of the voltage on the secondary winding of the transformer.

It can be used in all power supplies needing high efficiency, like:

- Chargers
- Adapters
- Asymmetrical half-bridge flyback power supplies
- Flyback power supplies with very low and/or variable output voltage

### 4 Ordering information

Table 1. Ordering information

Type number	Package		Version
	Name	Description	
TEA2093TS/1	TSOP6	plastic surface-mounted package; 6 leads	SOT457

### 5 Marking

Table 2. Marking codes

Type number	Marking code
TEA2093TS/1	TEA2093

6 Block diagram

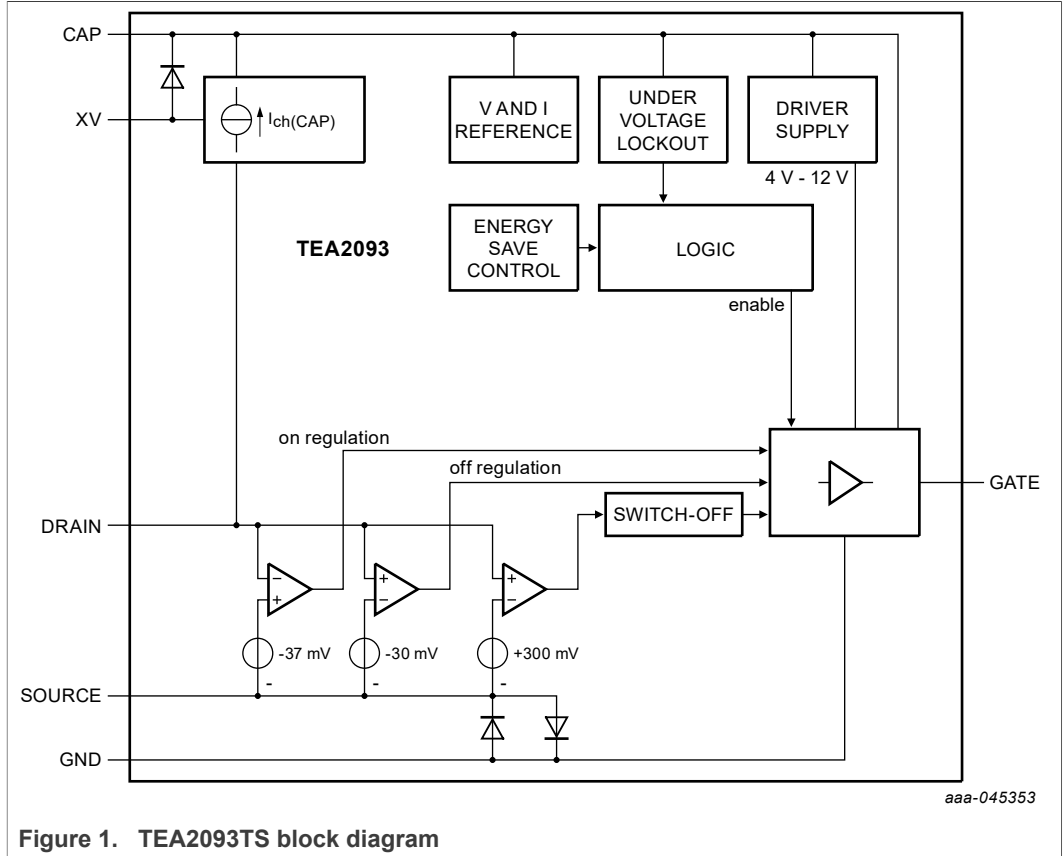


Figure 1. TEA2093TS block diagram

## 7 Pinning information

### 7.1 Pinning

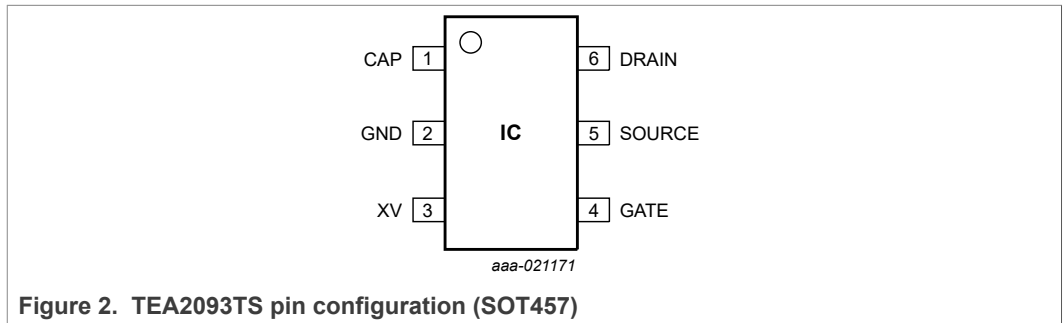


Figure 2. TEA2093TS pin configuration (SOT457)

### 7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
CAP	1	capacitor input for internal supply voltage
GND	2	ground
XV	3	external supply input
GATE	4	gate driver output for SR MOSFET
SOURCE	5	source sense input of SR MOSFET
DRAIN	6	drain sense input of SR MOSFET



**8.4 Synchronous rectification (DRAIN and SOURCE pins)**

The IC senses the voltage difference between the drain sense (DRAIN pin) and the source sense (SOURCE pin) connections. This drain source differential voltage of the SR MOSFET is used to drive the gate of the SR MOSFET.

In the regulation phase, the IC regulates the difference between the drain and the source sense inputs to an absolute level of 37 mV. When the absolute difference exceeds 37 mV ( $V_{reg(drv)}$ ), the gate driver output increases the gate voltage of the external SR MOSFET until the 37 mV level is reached. The SR MOSFET does not switch off at low current.

When the absolute difference is < 30 mV, the gate driver output decreases the gate voltage of the external SR MOSFET. The voltage waveform on the SR MOSFET gate follows the waveform of the current through the SR MOSFET. When the current through the SR MOSFET reaches zero, the SR MOSFET is quickly switched off.

After SR MOSFET switch-off, the drain voltage increases. When the drain voltage exceeds 300 mV, a low ohmic gate pull-down of 7 Ω keeps the gate of the SR MOSFET switched off.

**8.5 Gate driver (GATE pin)**

The gate driver circuit charges the gate of the external SR MOSFET during the rising part of the current. The driver circuit discharges the gate during the falling part of the current. The gate driver has a source capability of typically 0.50 A and a sink capability of typically 0.65 A, allowing fast turn-on and fast turn-off of the external SR MOSFET.

The maximum output voltage of the driver is limited to 12 V. This high output voltage drives all MOSFET brands to the minimum on-state resistance. In applications where the IC is supplied with 5 V, the maximum output voltage of the driver is 4.2 V and logic level SR MOSFETs can be used (see [Figure 3](#)).

The IC is self-supplying in applications with high-side rectification or in battery-charging applications with an output voltage below 4.7 V. When the XV pin is connected to ground for driving standard SR MOSFETs, the driver is regulated to 9 V. When the XV pin is connected to the converter output for driving logic-level SR MOSFETs, the driver is regulated to 4 V if the output voltage is below 4.7 V.

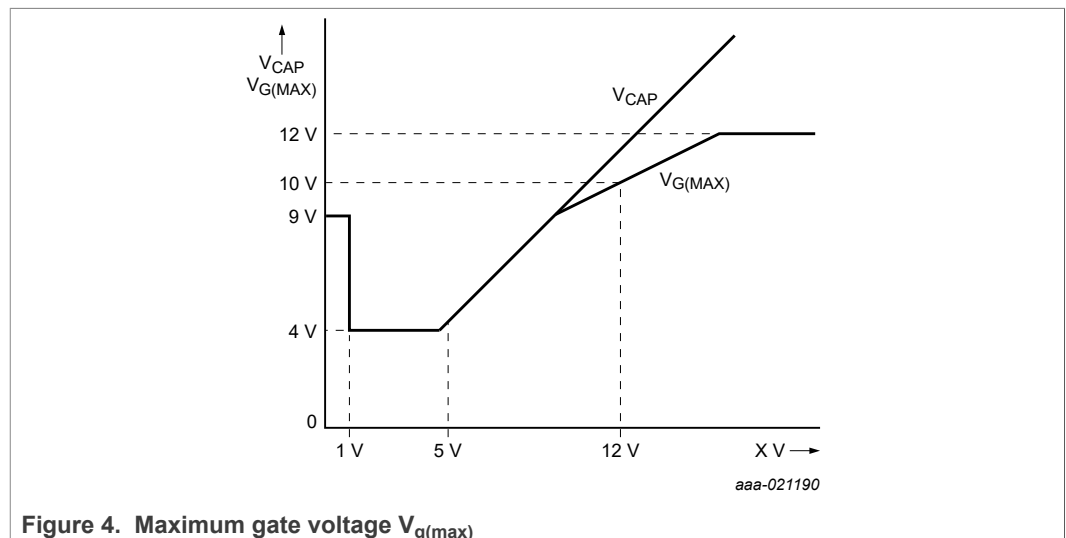


Figure 4. Maximum gate voltage  $V_{g(max)}$

During start-up conditions ( $V_{CAP} < V_{start(CAP)}$ ) and UVLO, the driver output voltage is actively pulled low.

## 8.6 Source sense (SOURCE pin)

The IC is equipped with an additional source sense pin (SOURCE). This pin is used for measuring the drain-to-source voltage of the external SR MOSFET. The source sense input must be connected as close as possible to the SOURCE pin of the external SR MOSFET. It minimizes errors, caused by voltage differences on PCB tracks due to parasitic inductance in combination with large  $di/dt$  values.

## 9 Limiting values

**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134). All voltages are measured with respect to ground (pin 2); positive currents flow into the chip. Voltage ratings are valid provided other ratings are not violated; current ratings are valid provided the other ratings are not violated.*

Symbol	Parameter	Conditions	Min	Max	Unit
<b>Voltages</b>					
$V_{XV}$	voltage on pin XV		-0.4	+38	V
$V_{sense(DRAIN)}$	sense voltage on pin DRAIN		-0.8	+120	V
$V_{sense(SOURCE)}$	sense voltage on pin SOURCE		-0.4	+0.4	V
<b>Currents</b>					
$I_{XV}$	current on pin XV	peak current	-	0.5	A
<b>General</b>					
$P_{tot}$	total power dissipation	$T_{amb} = 90\text{ °C}$	-	300	mW
$T_{stg}$	storage temperature		-55	+150	°C
$T_j$	junction temperature		-40	+150	°C
<b>Electrostatic discharge (ESD)</b>					
$V_{ESD}$	electrostatic discharge voltage	class 2			
		human body model <sup>[1]</sup>	-	2000	V
		charged device model	-	500	V

[1] Equivalent to discharging a 100 pF capacitor through a 1.5 kΩ series resistor.

## 10 Thermal characteristics

**Table 5. Thermal characteristics**

Symbol	Parameter	Conditions	Typ	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	JEDEC test board	200	K/W
$R_{th(j-c)}$	thermal resistance from junction to case	JEDEC test board	115	K/W



## 11 Characteristics

**Table 6. Characteristics**

$-25\text{ }^{\circ}\text{C} < T_j < +125\text{ }^{\circ}\text{C}$ ;  $V_{XV} = 12\text{ V}$ ;  $C_{CAP} = 1\text{ }\mu\text{F}$ ;  $C_{GATE} = 10\text{ nF}$  (capacitor between the GATE and the GND pins); all voltages are measured with respect to ground (pin 2); currents are positive when flowing into the IC; unless otherwise specified. Limits are production tested at  $25\text{ }^{\circ}\text{C}$ . Statistical characterization in the temperature operating range ensure these limits.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Supply voltage management (XV and CAP pins)</b>						
$V_{\text{start(CAP)}}$	start voltage on pin CAP	$V_{XV} = 0\text{ V}$	3.55	3.70	3.90	V
$V_{\text{stop(CAP)}}$	stop voltage on pin CAP	$V_{XV} = 0\text{ V}$	3.45	3.60	3.80	V
$I_{\text{ch(CAP)}}$	charge current on pin CAP	$V_{XV} = 0\text{ V}$ ; $V_{\text{CAP}} = 7\text{ V}$ ; $V_{\text{DRAIN}} = 12\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$	-95	-70	-50	mA
		$V_{XV} = 2\text{ V}$ ; $V_{\text{CAP}} = 3.65\text{ V}$ ; $V_{\text{DRAIN}} = 12\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$	-95	-70	-50	mA
$V_{\text{I(CAP)}}$	input voltage on pin CAP	$V_{XV} = 0\text{ V}$ ; $V_{\text{DRAIN}} = 12\text{ V}$	8.70	9.20	9.60	V
		$V_{XV} = 2\text{ V}$ ; $V_{\text{DRAIN}} = 12\text{ V}$	3.80	4.00	4.15	V
		$V_{XV} = 5\text{ V}$	4.15	4.30	4.75	V
		$V_{XV} = 12\text{ V}$	11.0	11.3	11.7	V
$I_{\text{I(XV)}}$	input current on pin XV	power save operation; $V_{XV} = 5\text{ V}$	90	160	300	$\mu\text{A}$
		normal operation; without gate charge; $V_{XV} = 5\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$	1.35	1.60	1.85	mA
<b>Synchronous rectification sense input (DRAIN and SOURCE pins)</b>						
$V_{\text{reg(drv)}}$	driver regulation voltage	$V_{\text{SOURCE}} = 0\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$	-40	-37	-35	mV
$V_{\text{swoff}}$	switch-off voltage	$V_{\text{SOURCE}} = 0\text{ V}$ ; $T_j = 25\text{ }^{\circ}\text{C}$	200	300	400	mV
$t_{\text{d(act)(drv)}}$	driver activation delay time	$V_{\text{SOURCE}} = 0\text{ V}$ ; normal operation; time for step on $V_{\text{DRAIN}}$ (2 V to -0.5 V) to rising of $V_{\text{GATE}}$ at 10 % of end value	-	65	-	ns
$t_{\text{d(deact)(drv)}}$	driver deactivation delay time	$V_{\text{SOURCE}} = 0\text{ V}$ ; normal operation; time for step on $V_{\text{DRAIN}}$ (-0.5 V to 2 V) to falling of $V_{\text{GATE}}$ at 10 % begin value	-	40	-	ns

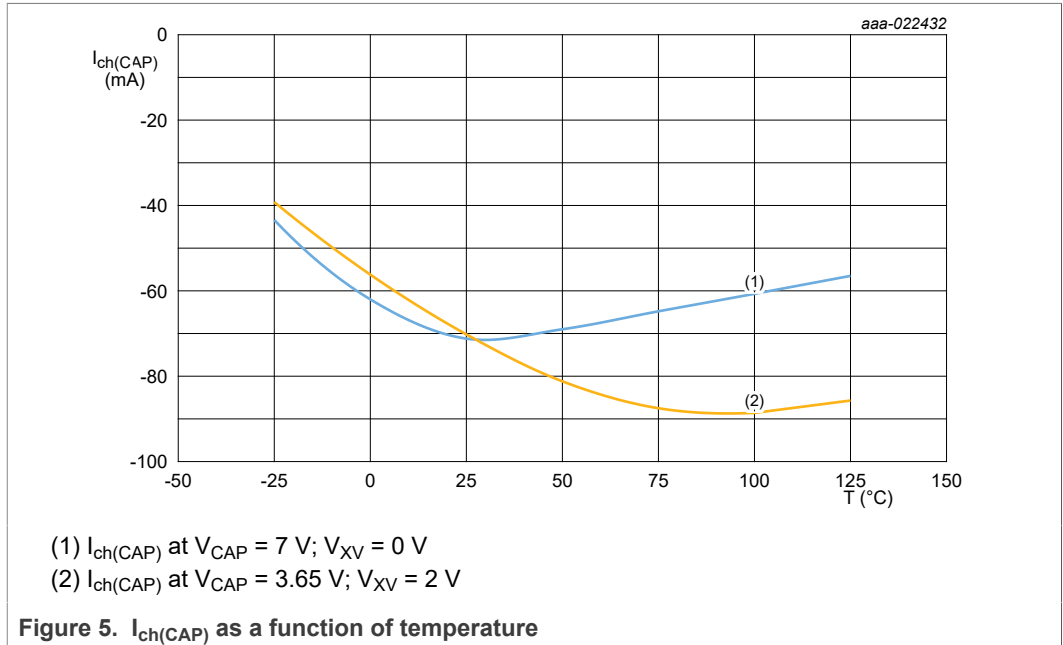
**Table 6. Characteristics...continued**

-25 °C < T<sub>J</sub> < +125 °C; V<sub>XV</sub> = 12 V; C<sub>CAP</sub> = 1 μF; C<sub>GATE</sub> = 10 nF (capacitor between the GATE and the GND pins); all voltages are measured with respect to ground (pin 2); currents are positive when flowing into the IC; unless otherwise specified. Limits are production tested at 25 °C. Statistical characterization in the temperature operating range ensure these limits.

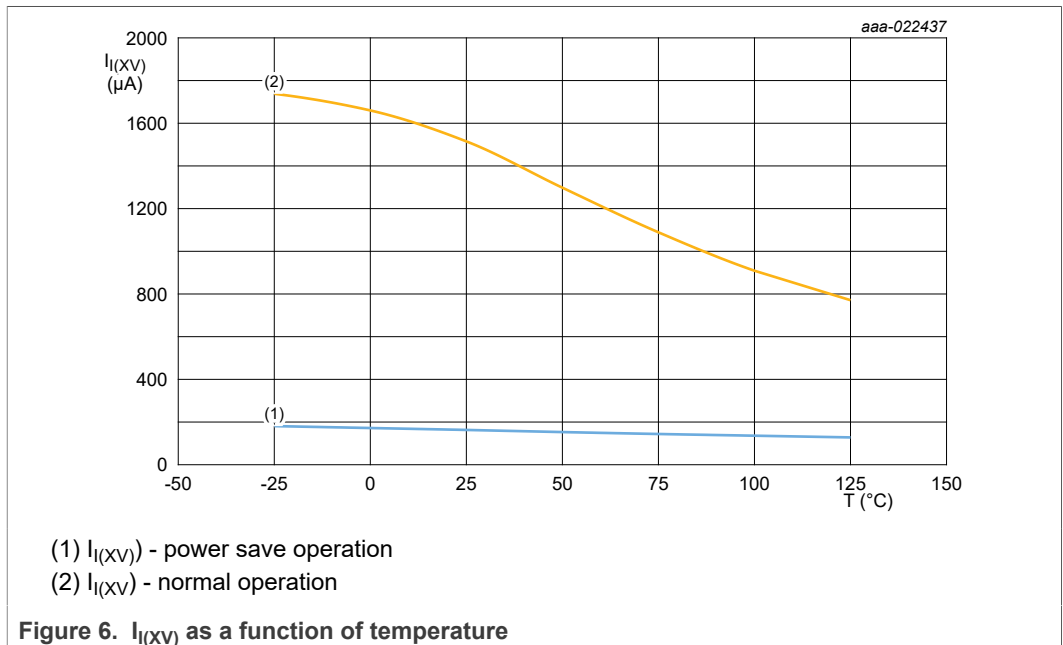
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Gate driver (GATE pin)</b>						
I <sub>source</sub>	source current	peak current				
		V <sub>XV</sub> = 5 V; V <sub>ds</sub> = -0.5 V; V <sub>g</sub> = 0 V	-	-0.13	-	A
		V <sub>XV</sub> = 12 V; V <sub>ds</sub> = -0.5 V; V <sub>g</sub> = 0 V	-	-0.50	-	A
I <sub>sink</sub>	sink current	regulation current				
		V <sub>XV</sub> = 5 V; V <sub>ds</sub> = 0 V; V <sub>g</sub> = 4 V	-	150	-	mA
		V <sub>XV</sub> = 12 V; V <sub>ds</sub> = 0 V; V <sub>g</sub> = 10 V	-	210	-	mA
		peak current				
		V <sub>XV</sub> = 5 V; V <sub>ds</sub> = 4 V; V <sub>g</sub> = 4 V	-	0.35	-	A
		V <sub>XV</sub> = 12 V; V <sub>ds</sub> = 4 V; V <sub>g</sub> = 4 V	-	0.65	-	A
R <sub>pd(G)</sub>	gate pull-down resistance	V <sub>DRAIN</sub> = 4 V; I <sub>GATE</sub> = 30 mA; V <sub>XV</sub> = 12 V; T <sub>J</sub> = 25 °C	6.00	6.80	7.60	Ω
V <sub>G(max)</sub>	maximum gate voltage	V <sub>XV</sub> = 0 V	7.80	8.90	9.60	V
		V <sub>XV</sub> = 2 V	3.75	3.95	4.15	V
		V <sub>XV</sub> = 5 V	4.00	4.20	4.40	V
		V <sub>XV</sub> = V <sub>CAP</sub> = 5 V	4.90	4.95	5.00	V
		V <sub>XV</sub> = 12 V	9.40	9.80	10.70	V
		V <sub>XV</sub> = 18 V to 38 V	11.80	12.30	12.70	V

### 11.1 Temperature curves

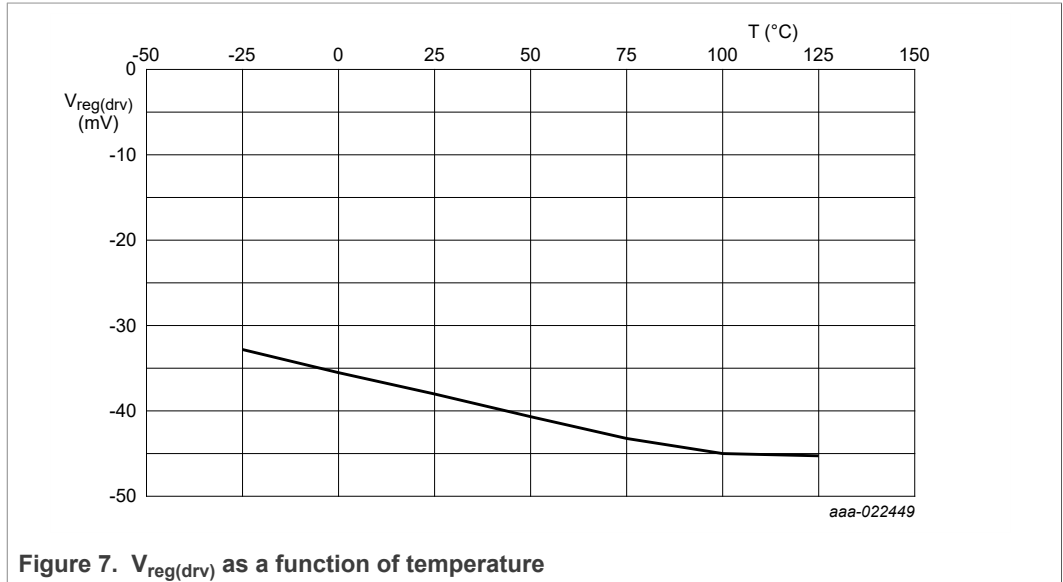
#### 11.1.1 Charge current (CAP pin)



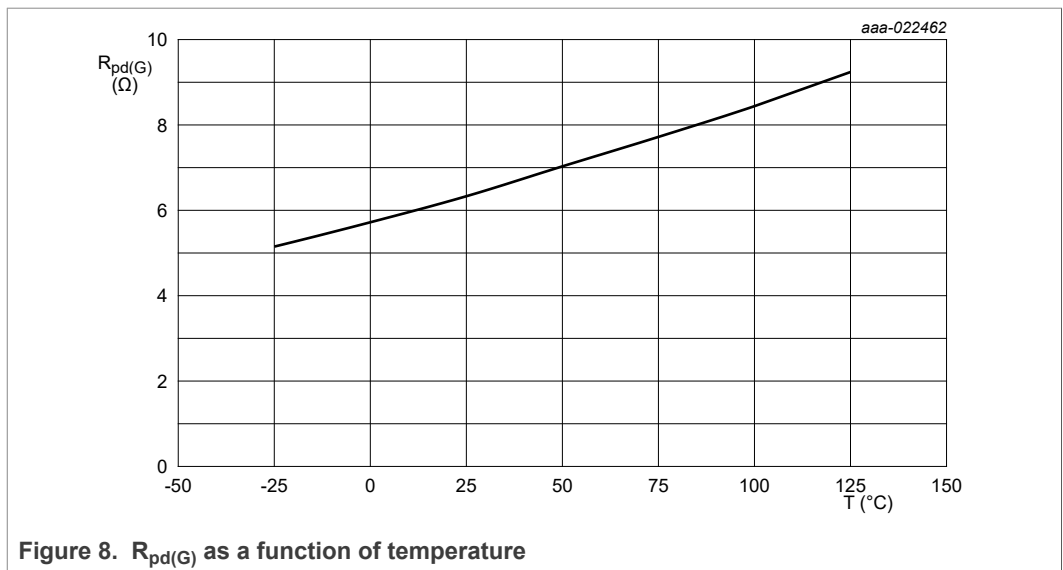
#### 11.1.2 Operating current (XV pin)



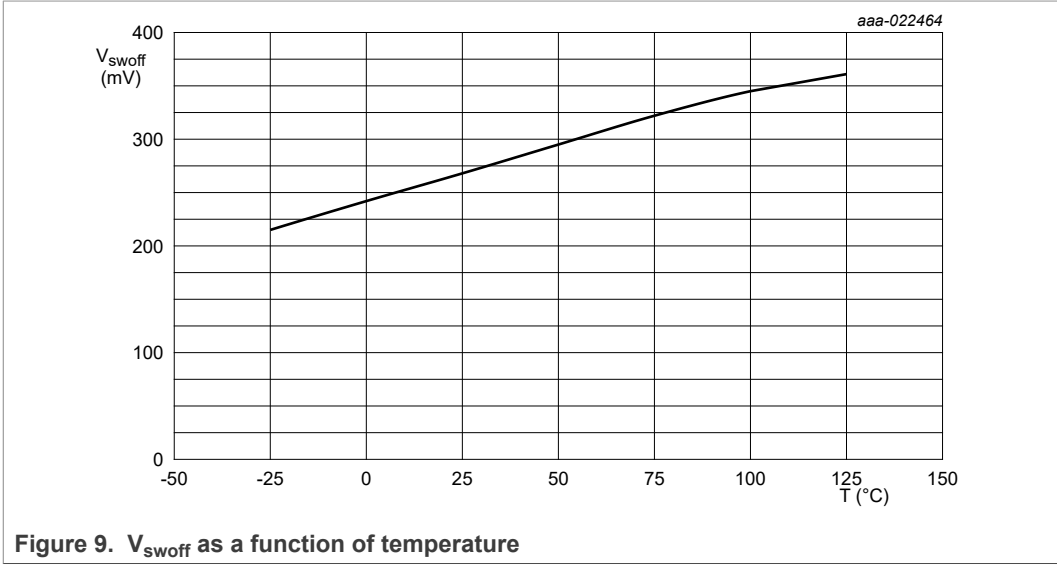
11.1.3 Driver regulation voltage



11.1.4 Gate pull-down resistance



11.1.5 Switch-off voltage



## 12 Application information

A flyback switched mode power supply with the TEA2093TS consists of a primary side controller with a primary switch, a transformer, and an output stage. To obtain low conduction loss rectification, an SR MOSFET is used in the output stage. The SR MOSFET can be placed low-side (see [Figure 3](#)) or can be placed high-side (see [Figure 10](#)). In the high-side application, the TEA2093TS is self-supplying. The capacitor on the CAP pin supplies the TEA2093TS. When the drain voltage is positive, it is charged via the DRAIN pin.

The gate drive voltage for the synchronous rectifier switch is derived from the voltage difference between the corresponding drain sense and source sense pins.

Special attention must be paid to the connection of the drain sense and source sense pins. The voltages measured on these pins are used for the gate drive voltage. Wrong measurement results in a less efficient gate drive because a gate voltage that is either too low or too high. The connections to these pins must not interfere with the power wiring.

The power wiring conducts currents with high di/dt values. It can easily cause measurement errors resulting from induced voltages due to parasitic inductances. The separate source sense pins make it possible to sense the source voltage of the external MOSFETs directly. So, the current carrying power ground tracks are not required.

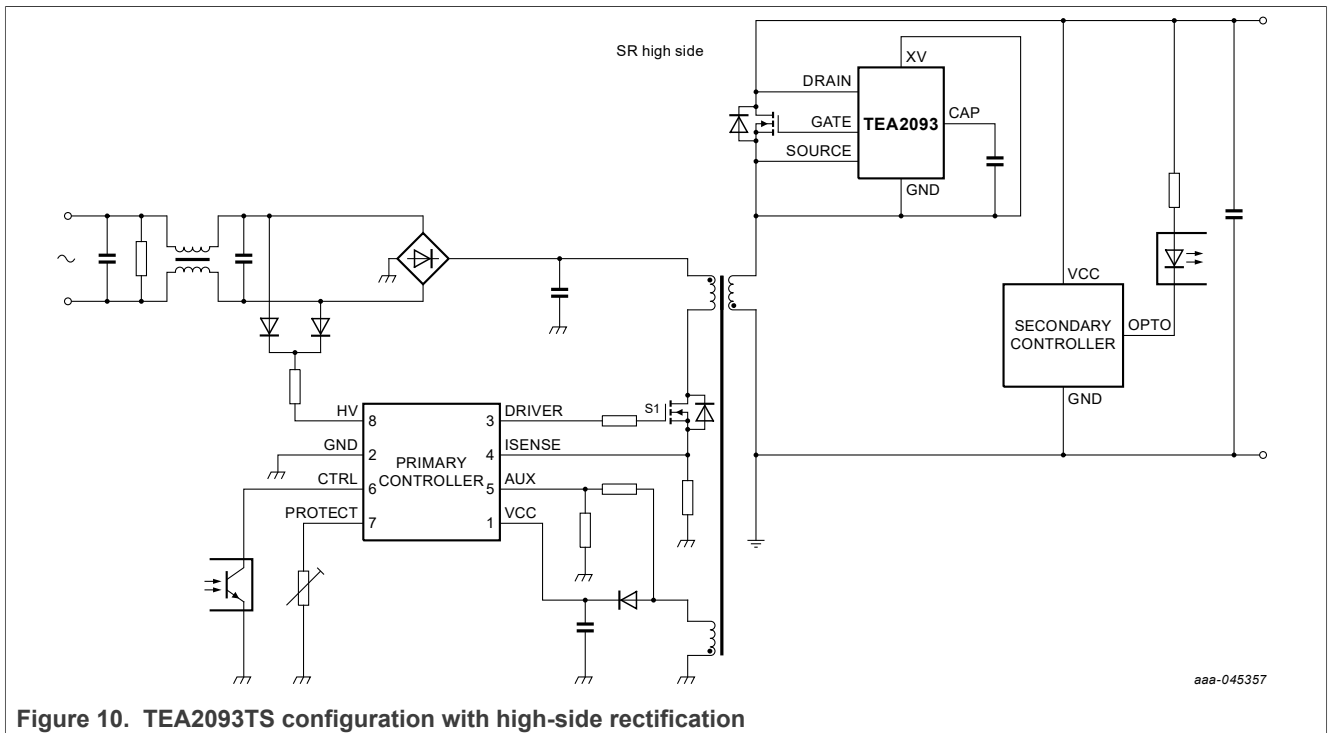


Figure 10. TEA2093TS configuration with high-side rectification

### 13 Package outline

Table 7.

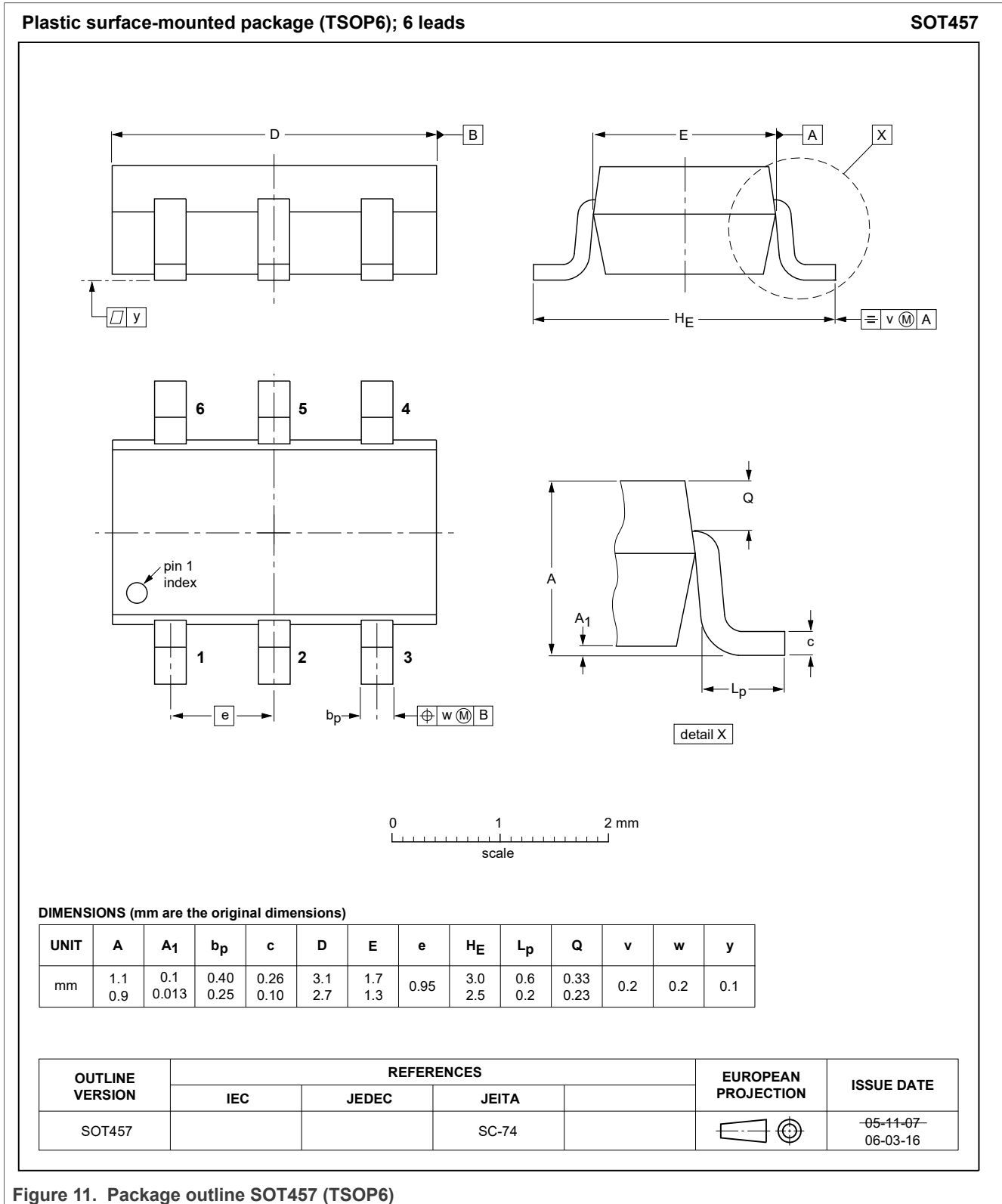


Figure 11. Package outline SOT457 (TSOP6)

## 14 Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
TEA2093TS v.1	20220607	Product data sheet	-	-



## 15 Legal information

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Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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